



SOT-89-3L Plastic-Encapsulate Transistors

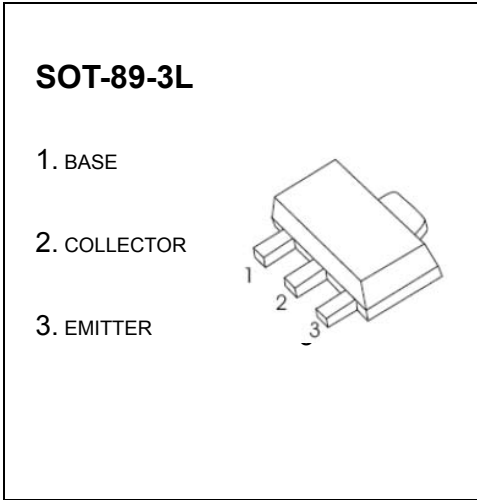
2SB1132 TRANSISTOR (PNP)

FEATURES

- Low $V_{CE(sat)}$
- Compliments 2SD1664

MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-32	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Continuous Collector Current	-1	A
I_{CP}	Pulsed Collector Current	2	A
P_C	Collector Power Dissipation	500	mW
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$



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ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-20V, I_E=0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-0.5	μA
DC current gain	h_{FE}	$V_{CE}=-3V, I_C=-100mA$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$		-0.2	-0.5	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-50mA, f=30MHz$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		20	30	pF

CLASSIFICATION OF h_{FE}

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking	BAP	BAQ	BAR

Typical Characteristics

2SB1132

